

2SA1566

Silicon PNP Epitaxial

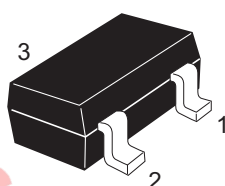
REJ03G0642-0200
(Previous ADE-208-1021)
Rev.2.00
Aug.10.2005

Application

Low frequency amplifier

Outline

RENESAS Package code: PLSP0003ZB-A
(Package name: MPAK)



- 1. Emitter
- 2. Base
- 3. Collector

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CB0}	-120	V
Collector to emitter voltage	V_{CE0}	-120	V
Emitter to base voltage	V_{EB0}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	—	—	V	$I_C = -10\ \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	—	—	V	$I_C = -1\ mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10\ \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	μA	$V_{CB} = -70\ V, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	μA	$V_{EB} = -2\ V, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800		$V_{CE} = -12\ V, I_C = -2\ mA^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.15	V	$I_C = -10\ mA, I_B = -1\ mA^{*2}$
Base to emitter voltage	$V_{BE(sat)}$	—	—	-1.0	V	$I_C = -10\ mA, I_B = -1\ mA^{*2}$

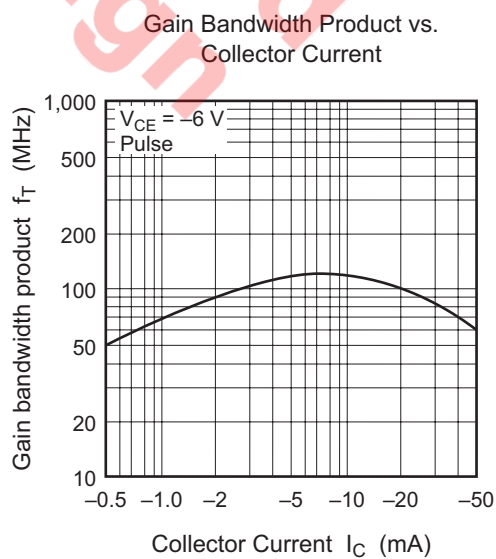
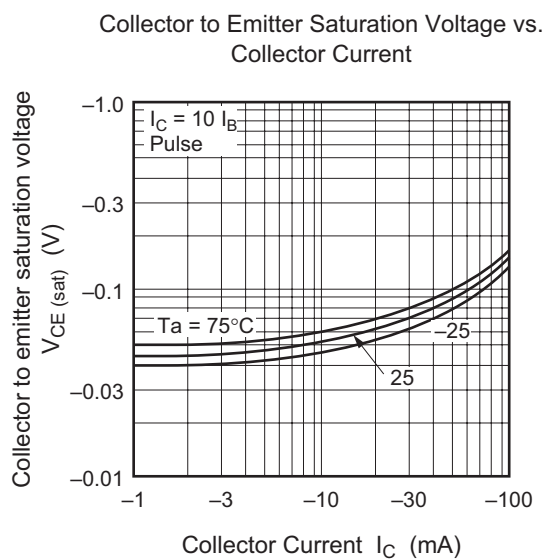
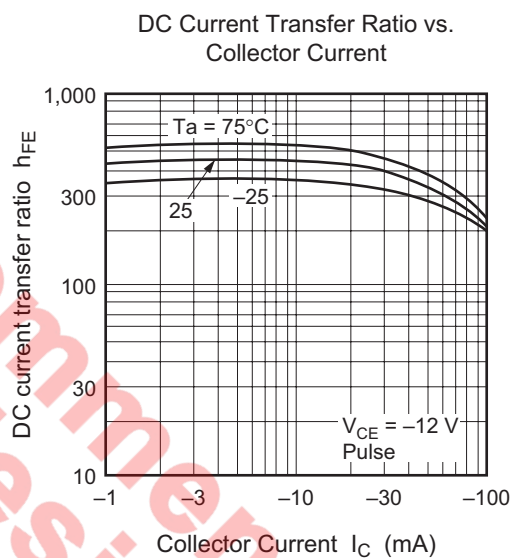
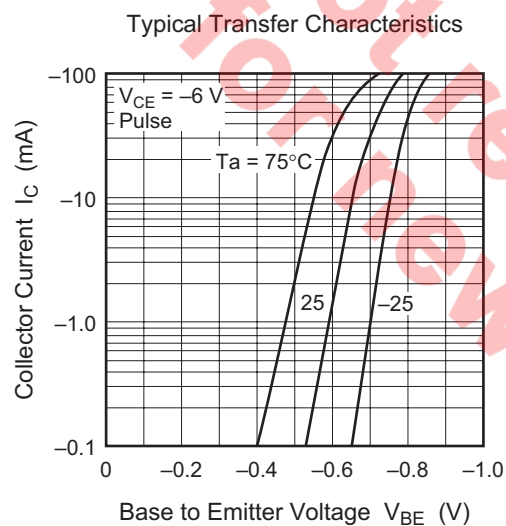
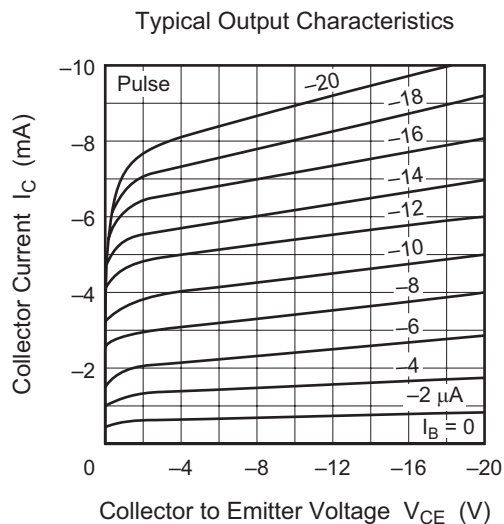
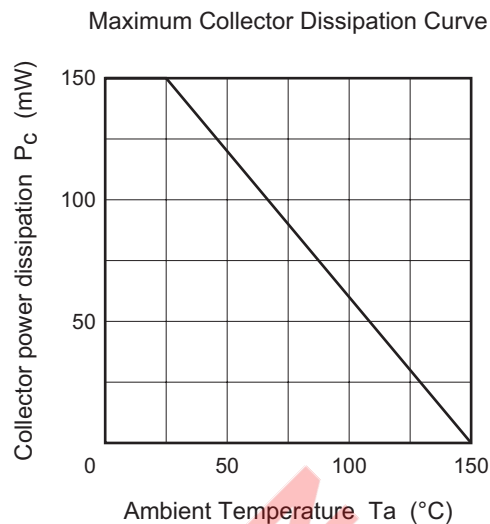
Notes: 1. The 2SA1566 is grouped by h_{FE} as follows.

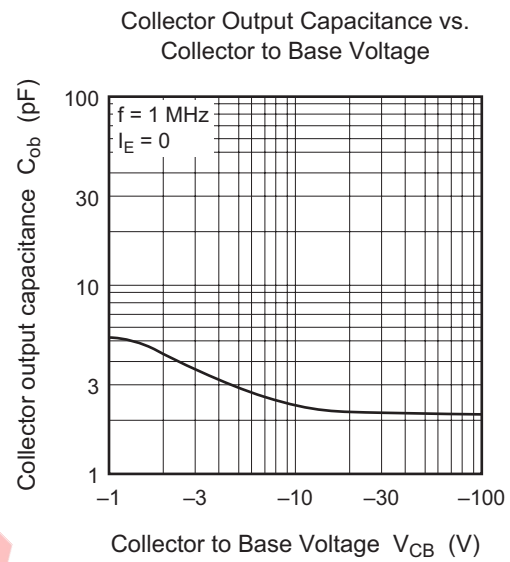
2. Pulse test

Grade	D	E
Mark	JID	JIE
h_{FE}	250 to 500	400 to 800

Not recommend
for new design

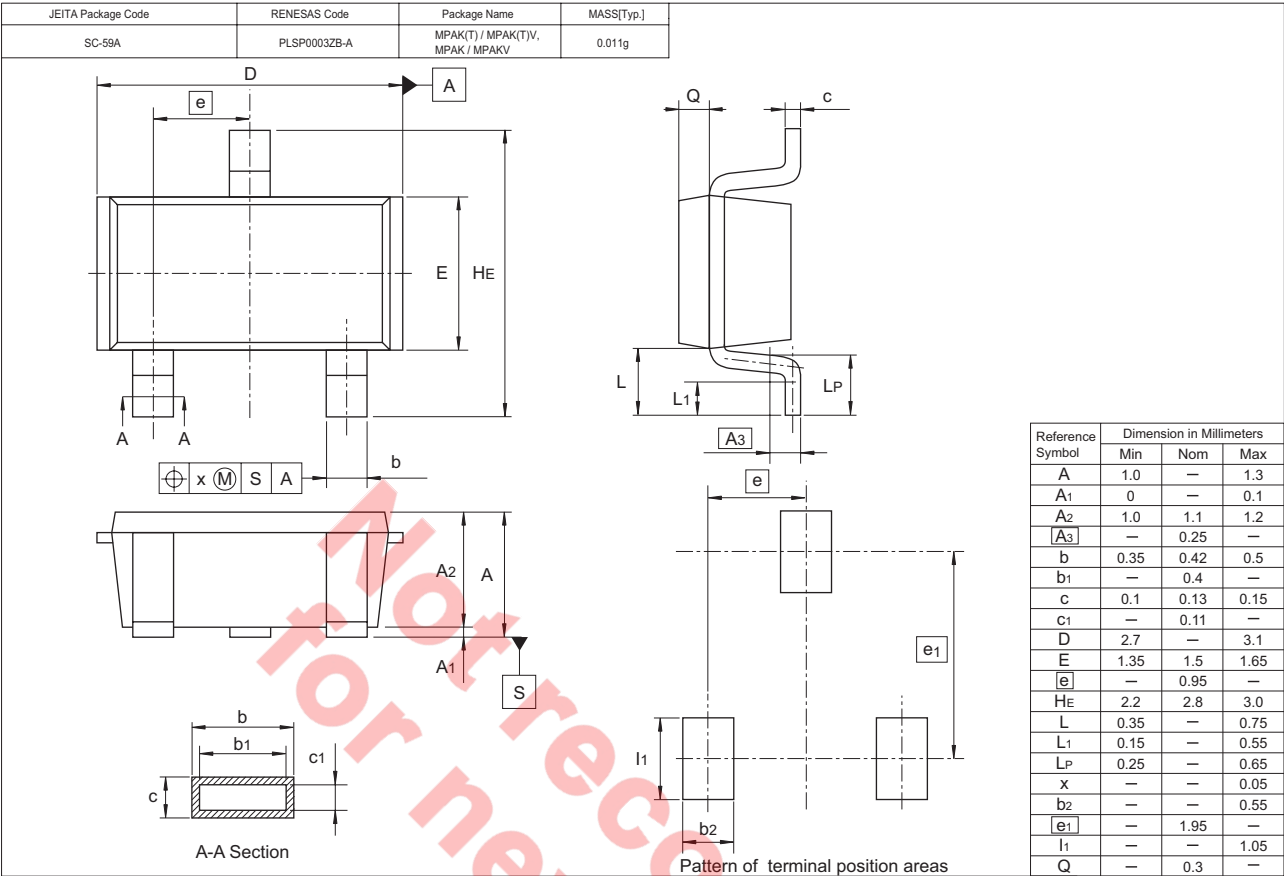
Main Characteristics





Not recommend
for new design

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA1566JIDTL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping
2SA1566JIETL-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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